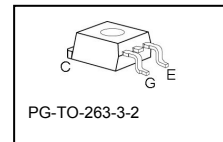
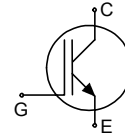


## Fast IGBT in NPT-technology

- Lower  $E_{off}$  compared to previous generation
- Short circuit withstand time – 10  $\mu$ s
- Designed for:
  - Motor controls
  - Inverter
  - SMPS
- NPT-Technology offers:
  - very tight parameter distribution
  - high ruggedness, temperature stable behaviour
  - parallel switching capability



- Qualified according to JEDEC<sup>1</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>

Type	$V_{CE}$	$I_C$	$E_{off}$	$T_j$	Marking	Package
SGB02N120	1200V	2A	0.11mJ	150°C	GB02N120	PG-TO-263-3-2

### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	1200	V
DC collector current	$I_C$	2	A
$T_C = 25^\circ\text{C}$		6.2	
$T_C = 100^\circ\text{C}$		2.8	
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	9.6	
Turn off safe operating area	-	9.6	
$V_{CE} \leq 1200\text{V}, T_j \leq 150^\circ\text{C}$			
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Avalanche energy, single pulse	$E_{AS}$	10	mJ
$I_C = 2\text{A}, V_{CC} = 50\text{V}, R_{GE} = 25\Omega$ , start at $T_j = 25^\circ\text{C}$			
Short circuit withstand time <sup>2</sup>	$t_{SC}$	10	$\mu$ s
$V_{GE} = 15\text{V}, 100\text{V} \leq V_{CC} \leq 1200\text{V}, T_j \leq 150^\circ\text{C}$			
Power dissipation	$P_{tot}$	62	W
$T_C = 25^\circ\text{C}$			
Operating junction and storage temperature	$T_j, T_{stg}$	-55...+150	$^\circ\text{C}$
Soldering temperature (reflow soldering, MSL1)	$T_s$	245	

<sup>1</sup> J-STD-020 and JESD-022

<sup>2</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

**Thermal Resistance**

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		2.0	K/W
Thermal resistance, junction – ambient	$R_{thJA}$		40	

**Electrical Characteristic, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=100\mu A$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=2A$ $T_j=25\text{ °C}$ $T_j=150\text{ °C}$	2.5 -	3.1 3.7	3.6 4.3	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=100\mu A, V_{CE}=V_{GE}$	3	4	5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25\text{ °C}$ $T_j=150\text{ °C}$	- -	- -	25 100	$\mu A$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=2A$		1.5	-	S
<b>Dynamic Characteristic</b>						
Input capacitance	$C_{iss}$	$V_{CE}=25V,$	-	205	250	pF
Output capacitance	$C_{oss}$	$V_{GE}=0V,$	-	20	25	
Reverse transfer capacitance	$C_{riss}$	$f=1\text{ MHz}$	-	12	14	
Gate charge	$Q_{Gate}$	$V_{CC}=960V, I_C=2A$ $V_{GE}=15V$	-	11	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	7	-	nH
Short circuit collector current <sup>2)</sup>	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 10\mu s$ $100V\leq V_{CC}\leq 1200V,$ $T_j\leq 150\text{ °C}$	-	24	-	A

<sup>2)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

**Switching Characteristic, Inductive Load, at  $T_j=25\text{ }^\circ\text{C}$** 

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25\text{ }^\circ\text{C}$ , $V_{CC}=800\text{V}$ , $I_C=2\text{A}$ , $V_{GE}=15\text{V}/0\text{V}$ , $R_G=91\Omega$ , $L_{\sigma}^{(1)}=180\text{nH}$ , $C_{\sigma}^{(1)}=40\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	23	30	ns
Rise time	$t_r$		-	16	21	
Turn-off delay time	$t_{d(off)}$		-	260	340	
Fall time	$t_f$		-	61	80	
Turn-on energy	$E_{on}$		-	0.16	0.21	mJ
Turn-off energy	$E_{off}$		-	0.06	0.08	
Total switching energy	$E_{ts}$		-	0.22	0.29	

**Switching Characteristic, Inductive Load, at  $T_j=150\text{ }^\circ\text{C}$** 

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=150\text{ }^\circ\text{C}$ $V_{CC}=800\text{V}$ , $I_C=2\text{A}$ , $V_{GE}=15\text{V}/0\text{V}$ , $R_G=91\Omega$ , $L_{\sigma}^{(1)}=180\text{nH}$ , $C_{\sigma}^{(1)}=40\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	26	31	ns
Rise time	$t_r$		-	14	17	
Turn-off delay time	$t_{d(off)}$		-	290	350	
Fall time	$t_f$		-	85	102	
Turn-on energy	$E_{on}$		-	0.27	0.33	mJ
Turn-off energy	$E_{off}$		-	0.11	0.15	
Total switching energy	$E_{ts}$		-	0.38	0.48	

<sup>1)</sup> Leakage inductance  $L_{\sigma}$  and stray capacity  $C_{\sigma}$  due to dynamic test circuit in figure E.

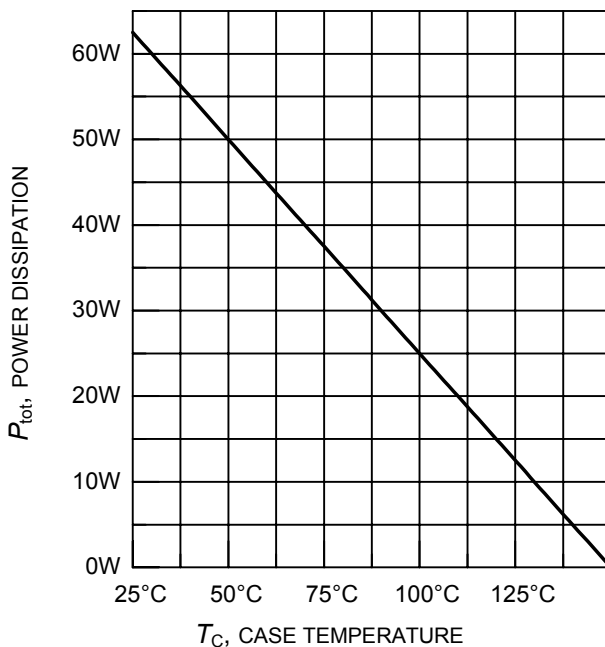


**Figure 1. Collector current as a function of switching frequency**

( $T_j \leq 150^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 91\Omega$ )

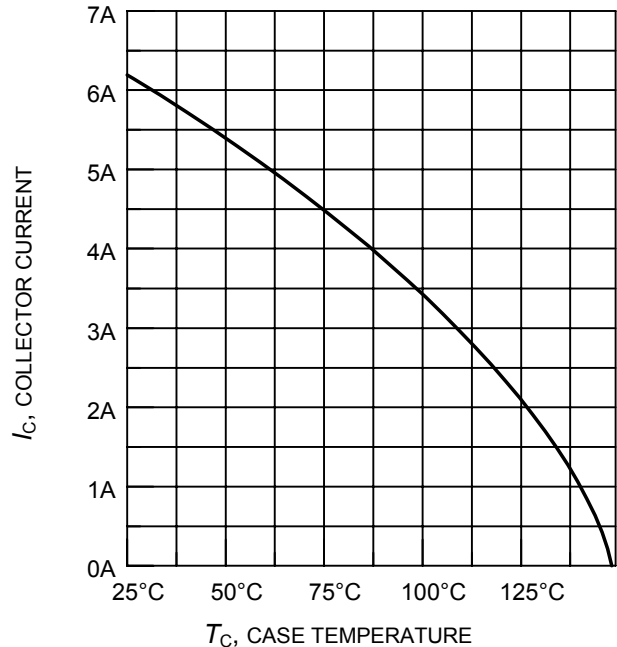


**Figure 2. Safe operating area**  
( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 150^\circ\text{C}$ )



**Figure 3. Power dissipation as a function of case temperature**

( $T_j \leq 150^\circ\text{C}$ )



**Figure 4. Collector current as a function of case temperature**

( $V_{GE} \leq 15\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )



**Figure 5. Typical output characteristics**  
( $T_j = 25^\circ\text{C}$ )



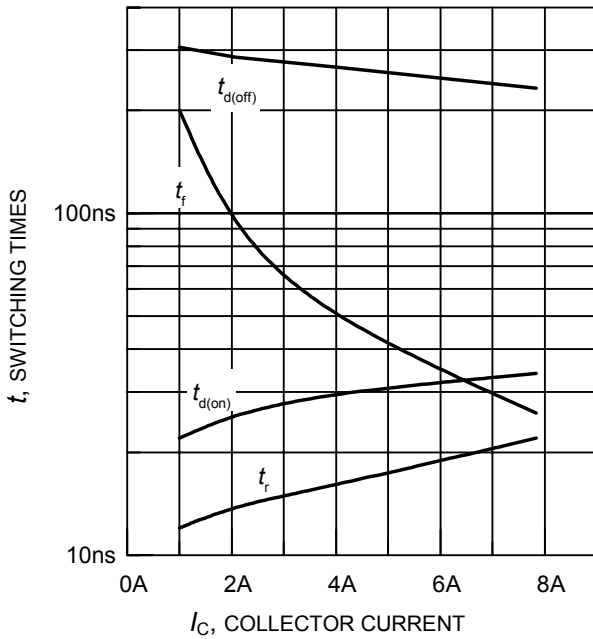
**Figure 6. Typical output characteristics**  
( $T_j = 150^\circ\text{C}$ )



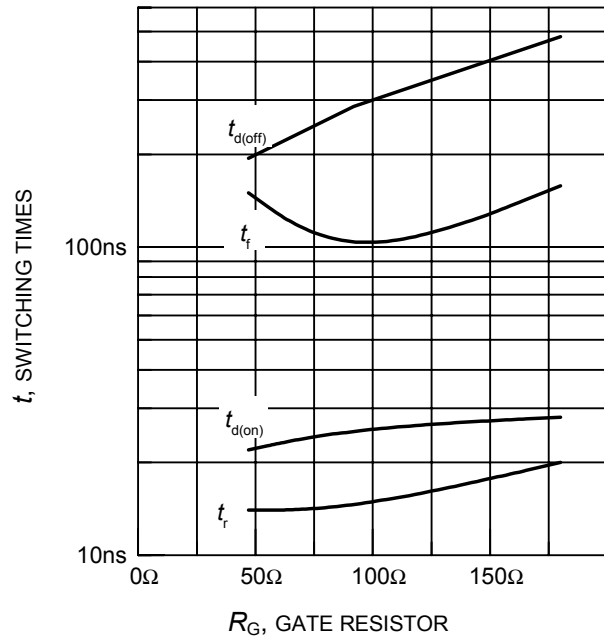
**Figure 7. Typical transfer characteristics**  
( $V_{CE} = 20\text{V}$ )



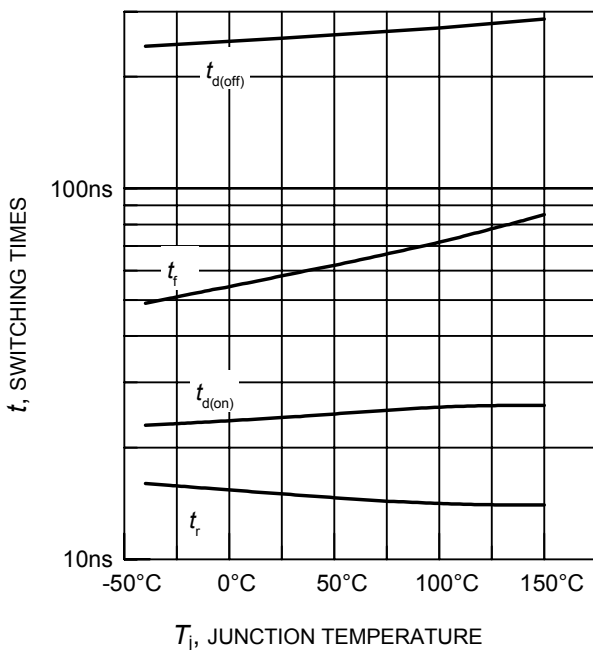
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



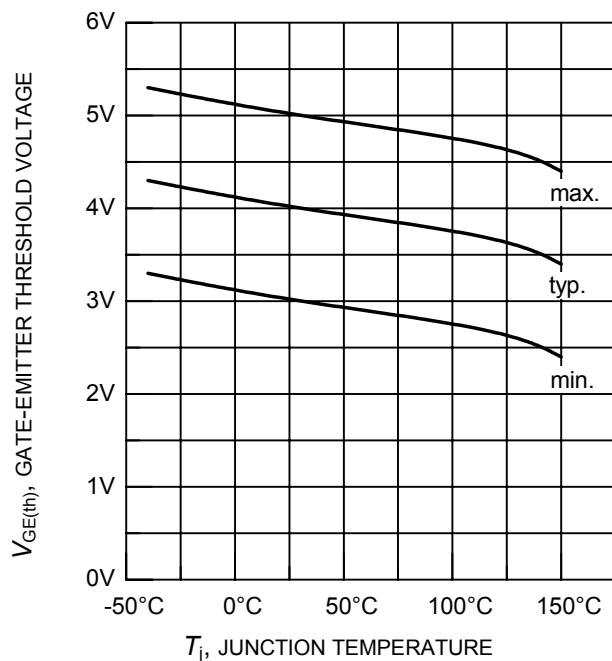
**Figure 9. Typical switching times as a function of collector current**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  
 $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 91\Omega$ ,  
 dynamic test circuit in Fig.E)



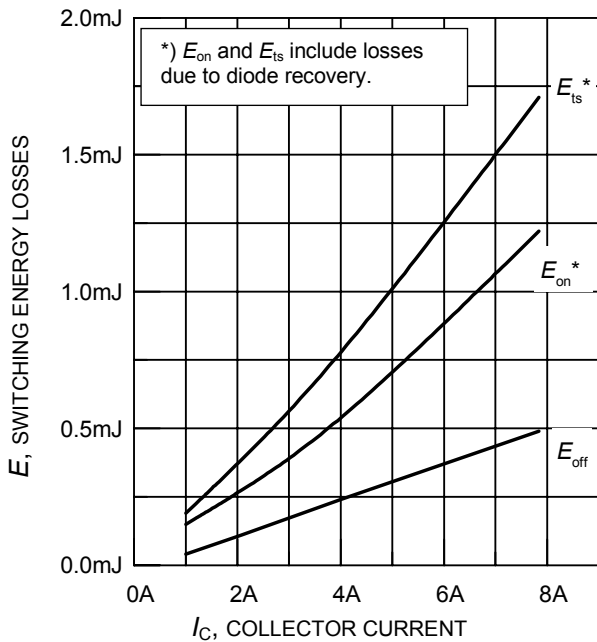
**Figure 10. Typical switching times as a function of gate resistor**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  
 $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 2\text{A}$ ,  
 dynamic test circuit in Fig.E)



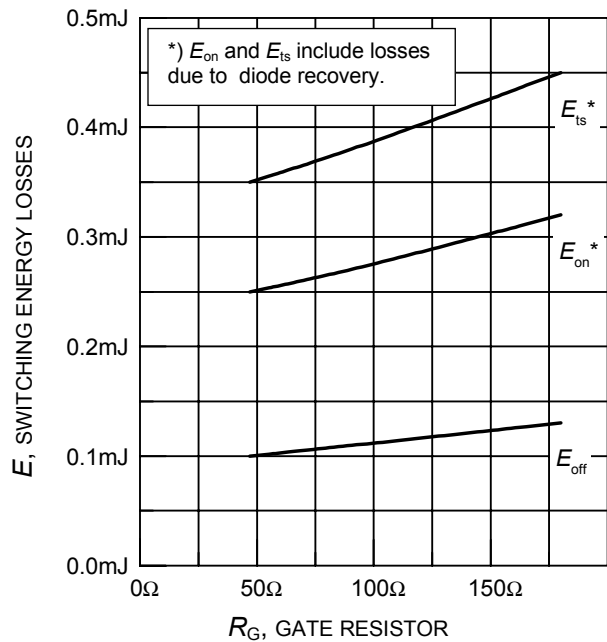
**Figure 11. Typical switching times as a function of junction temperature**  
 (inductive load,  $V_{CE} = 800\text{V}$ ,  
 $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 2\text{A}$ ,  $R_G = 91\Omega$ ,  
 dynamic test circuit in Fig.E)



**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
 ( $I_C = 0.3\text{mA}$ )



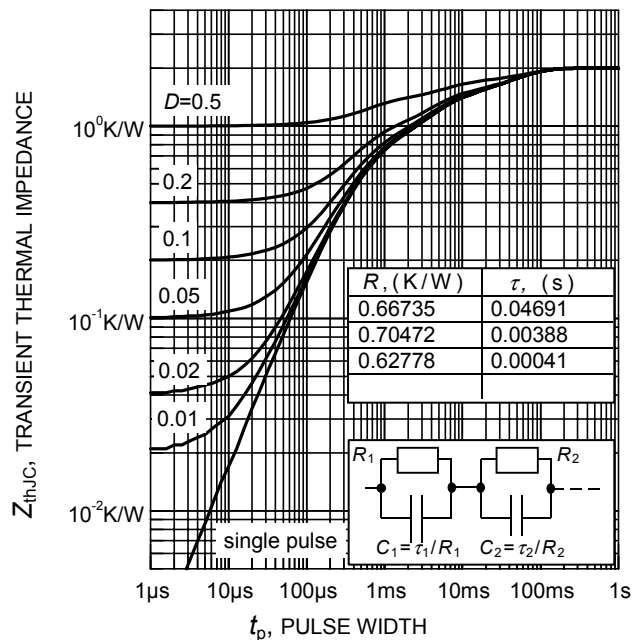
**Figure 13. Typical switching energy losses as a function of collector current**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 91\Omega$ , dynamic test circuit in Fig.E )



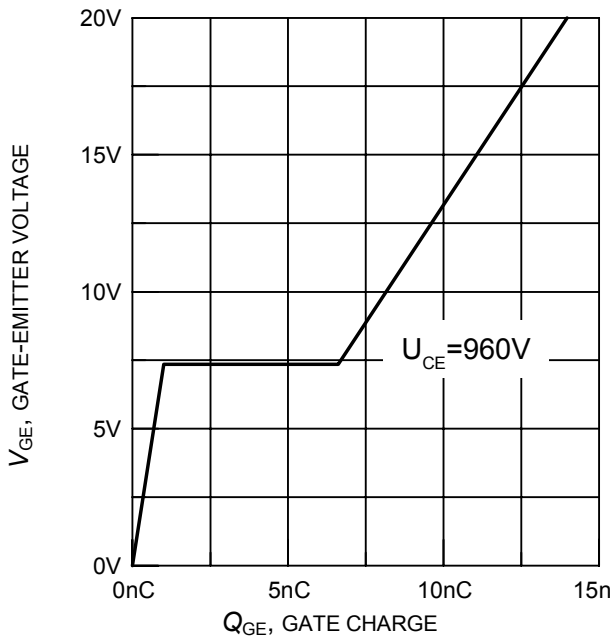
**Figure 14. Typical switching energy losses as a function of gate resistor**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 2\text{A}$ , dynamic test circuit in Fig.E )



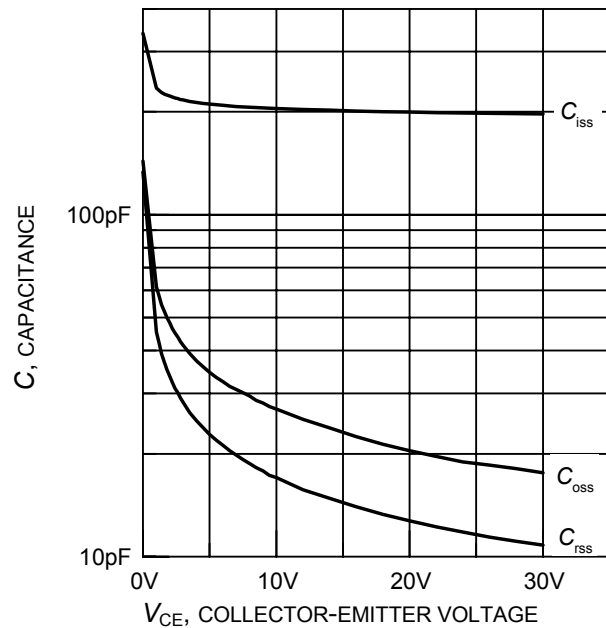
**Figure 15. Typical switching energy losses as a function of junction temperature**  
 (inductive load,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 2\text{A}$ ,  $R_G = 91\Omega$ , dynamic test circuit in Fig.E )



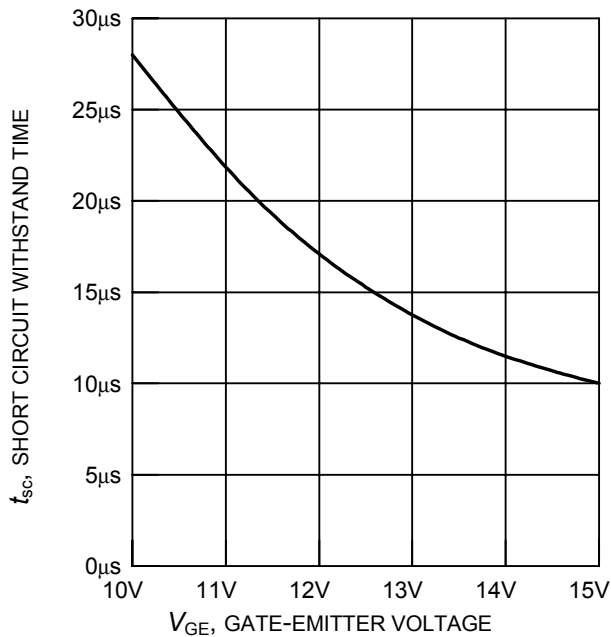
**Figure 16. IGBT transient thermal impedance as a function of pulse width**  
 ( $D = t_p / T$ )



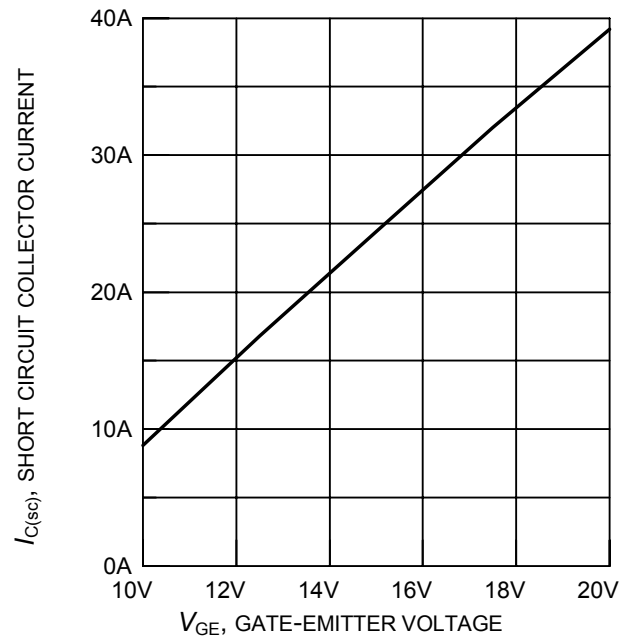
**Figure 17. Typical gate charge**  
( $I_C = 2A$ )



**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE} = 0V, f = 1MHz$ )



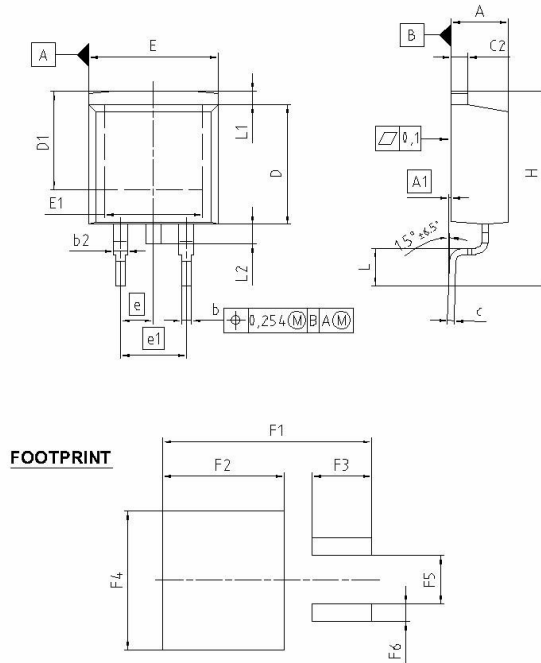
**Figure 19. Short circuit withstand time as a function of gate-emitter voltage**  
( $V_{CE} = 1200V, \text{start at } T_j = 25^\circ C$ )



**Figure 20. Typical short circuit collector current as a function of gate-emitter voltage**  
( $100V \leq V_{CE} \leq 1200V, T_C = 25^\circ C, T_j \leq 150^\circ C$ )



PG-TO263-3-2



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.572	0.169	0.180
A1	0.000	0.254	0.000	0.010
b	0.850	0.850	0.033	0.033
b2	0.950	1.321	0.037	0.052
c	0.330	0.850	0.013	0.033
c2	0.170	1.400	0.046	0.055
D	8.509	9.450	0.335	0.372
D1	7.100	-	0.280	-
E	9.800	10.312	0.386	0.406
E1	6.500	-	0.256	-
e	2.540		0.100	
e1	5.080		0.200	
N	2		2	
H	14.605	15.875	0.575	0.625
L	2.200	3.000	0.087	0.119
L1	-	1.600	-	0.063
L2	1.000	1.778	0.039	0.070
F1	16.050	16.250	0.632	0.640
F2	9.300	9.500	0.366	0.374
F3	4.500	4.700	0.177	0.185
F4	10.700	10.900	0.421	0.429
F5	3.630	3.830	0.143	0.151
F6	1.100	1.300	0.043	0.051

REFERENCE  
JEDEC TO263

SCALE  
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EUROPEAN PROJECTION

ISSUE DATE  
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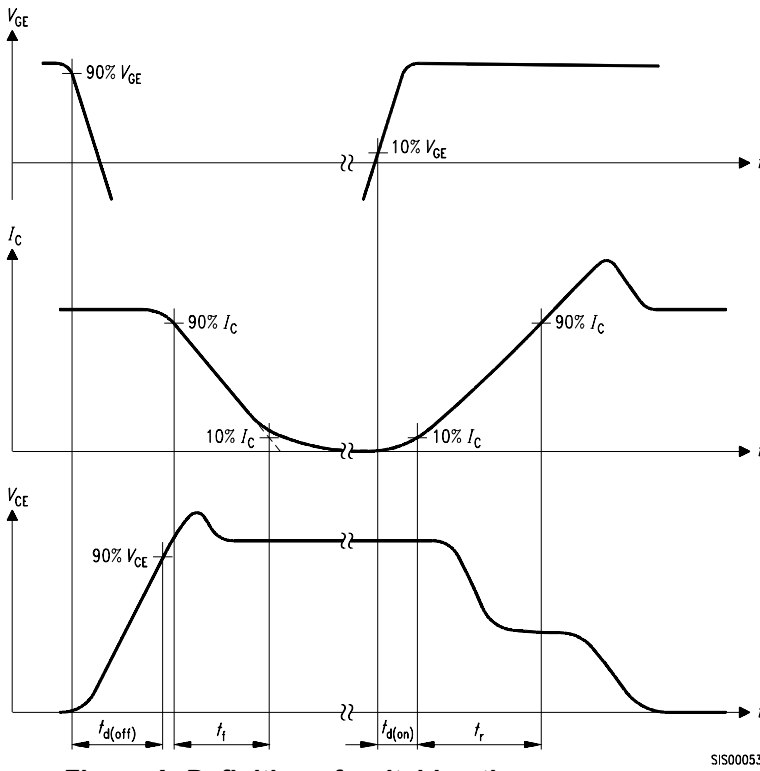


Figure A. Definition of switching times

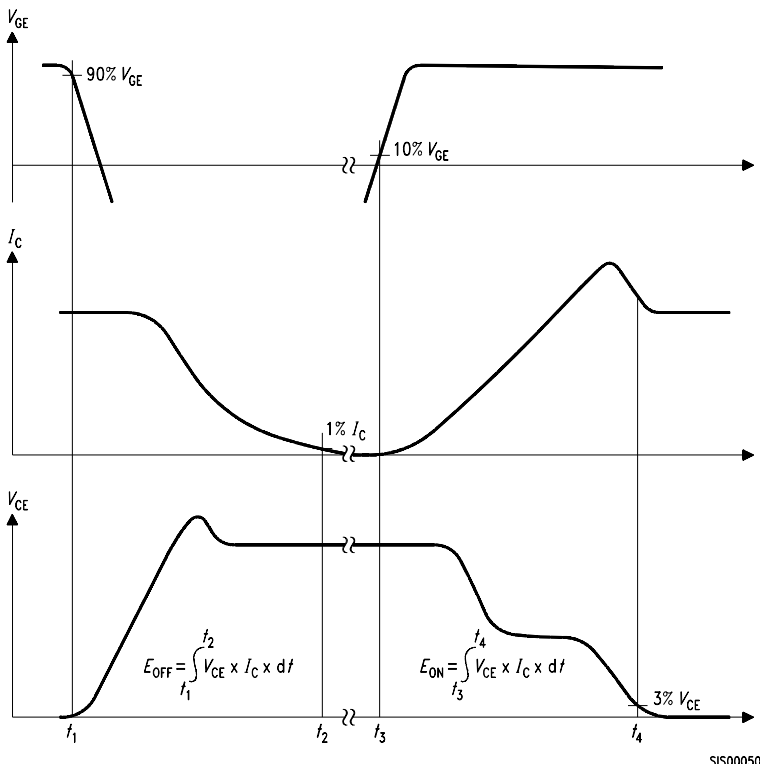


Figure B. Definition of switching losses

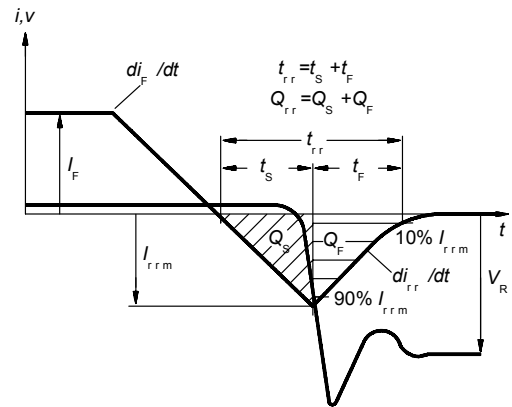


Figure C. Definition of diodes switching characteristics

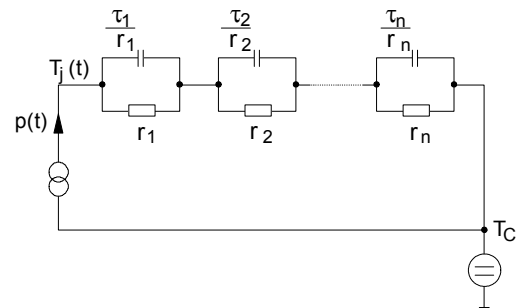


Figure D. Thermal equivalent circuit

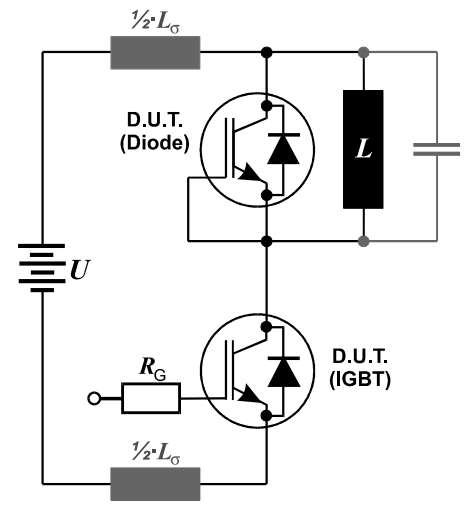


Figure E. Dynamic test circuit  
Leakage inductance  $L_\sigma=180\text{nH}$ ,  
and stray capacity  $C_\sigma=40\text{pF}$ .

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